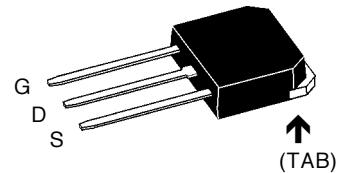
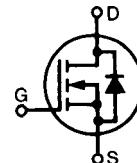


HiPerFET™

N-Channel Enhancement Mode

IXTJ 36N20

 $V_{DSS} = 200$ V $I_{D25} = 36$ A $R_{DS(on)} = 70$ mΩ $t_{rr} < 200$ ns

G = Gate, D = Drain,
S = Source, TAB = Drain

Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	200	V	
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1$ MΩ	200	V	
V_{GS}	Continuous	±20	V	
V_{GSM}	Transient	±30	V	
I_{D25}	$T_C = 25^\circ\text{C}$	36	A	
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	144	A	
I_{AR}		36	A	
E_{AR}	$T_C = 25^\circ\text{C}$	19	mJ	
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100$ A/μs, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2$ Ω	5	V/ns	
P_D	$T_C = 25^\circ\text{C}$	300	W	
T_J		-55 ... +150	°C	
T_{JM}		150	°C	
T_{stg}		-55 ... +150	°C	
M_d	Mounting torque	1.13/10	Nm/lb.in.	
Weight		5	g	
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	°C	

Symbol	Test Conditions	Characteristic Values		
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.
V_{DSS}	$V_{GS} = 0$ V, $I_D = 250$ μA	200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4$ mA	2		4 V
I_{GSS}	$V_{GS} = \pm 20$ V _{DC} , $V_{DS} = 0$		±100	nA
I_{DSS}	$V_{DS} = 0.8 V_{DSS}$ $V_{GS} = 0$ V	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	25 250	μA μA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 18$ A Pulse test, $t \leq 300$ μs, duty cycle d ≤ 2 %		70	mΩ

Features

- International standard package JEDEC TO-247 AD
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- High commutating dv/dt rating
- Fast switching times

Applications

- Switch-mode and resonant-mode power supplies
- Motor controls
- Uninterruptible Power Supplies (UPS)
- DC choppers

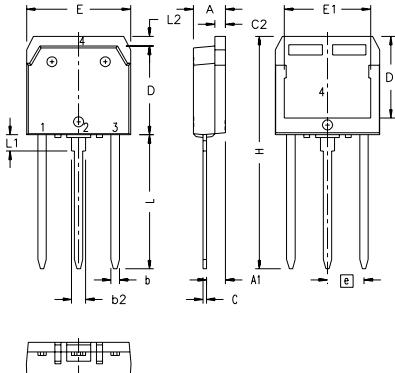
Advantages

- Easy to mount with 1 screw (isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10 \text{ V}; I_D = 0.5 I_{D25}$, pulse test	12	22	S
C_{iss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	2970		pF
C_{oss}		530		pF
C_{rss}		180		pF
$t_{d(on)}$	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2 \Omega$ (External)		29	ns
t_r			130	ns
$t_{d(off)}$			110	ns
t_i			98	ns
$Q_{g(on)}$	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$	106	140	nC
Q_{gs}		24	40	nC
Q_{gd}		43	74	nC
R_{thJC}			0.65	K/W
R_{thCK}		0.24		K/W

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_s	$V_{GS} = 0 \text{ V}$		36	A
I_{SM}	Repetitive; pulse width limited by T_{JM}		144	A
V_{SD}	$I_F = I_S, V_{GS} = 0 \text{ V},$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$		1.8	V
t_{rr}	$I_F = I_S, -di/dt = 100 \text{ A}/\mu\text{s},$ $V_R = 100 \text{ V}$		200	ns
			350	ns

Leaded TO-268 Package Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	1.365	1.395	34.67	35.43
L	.780	.800	19.81	20.32
L1	.079	.091	2.00	2.30
L2	.039	.045	1.00	1.15

NOTE: ALL METAL AREA ARE SOLDER PLATED.

- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - DRAIN (COLLECTOR)